L Number	Hits	Search Text	DB	Time stamp
4	10	(sic or silicon adj carbide) near2 seed same (boule or ingot) and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 10:55
5	39	(sic or silicon adj carbide) near2 seed same diameter	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 11:22
6	9	(sic or silicon adj carbide) near2 seed and (gan or gallium adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 11:25
8	14	(sic or silicon adj carbide) near2 substrate and (gan or gallium adj nitride) same (ingot or boule)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 11:30
9	40	(sic or silicon adj carbide) near2 seed and diamond	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 11:31
10	8	(sic or silicon adj carbide) near2 seed same diamond	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 11:31
-	108	((pressure same (vary or varying or varied or varing or alternated or alternating or alternate)) and (sic or silicon adj carbide)) and (117/$4.ccls. or 427/$4.ccls.) and (carbon or silicon) near3 source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 09:44
-	84	((sic or silicon adj carbide) and 117/84-109.ccls.) and source and cycle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 10:01
-	55	((sic or silicon adj carbide) and 117/84-109.ccls.) and puls$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 11:19
-	54	(partial adj pressure) same (silicon or carbon or si or c) and (sic or silicon adj carbide) and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 14:33
-	38	(partial adj pressure) same (silicon or carbon) and (sic or silicon adj carbide) and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 15:45
-	28	(sic or silicon adj carbide) same (npn or pnp) and (438/$4.ccls. or 117/$4.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 15:19
-	8	sccm near10 (silicon or carbon) and (sic or silicon adj carbide) and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 15:54

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70	(sic or silicon adj carbide) near3 seed and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 16:02
13	attach$4 near3 coefficient and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 09:35
54	((sic or silicon adj carbide) and 117/84-109.ccls.) and flow adj rate same (silicon or carbon) same (carbide or sic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 17:34
37	attach$4 near3 coefficient and (silicon adj carbide or sic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 09:54
9	attach$4 adj coefficient and (silicon adj carbide or sic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 11:59
18	superlattice same (sic or silicon adj carbide) same dop$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 13:35
16	superlattice same (sic or silicon adj carbide) and cycle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 15:04
80	superlattice same (silicon adj carbide or sic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 17:46
46	(ald or ale or atomic adj layer adj (epitax$4 or deposit$4)) same (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 09:40
38	attachment near2 coefficient same (gas$4 or pressure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:01
11	attachment near2 coefficient and (silicon adj carbide or sic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:05
4	attachment near2 coefficient same (silicon adj carbide or sic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:12
20	((constant$4 or stead$4) near3 (gas or reactant or pressure or flow) same (sic or silicon adj carbide)) and puls$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 11:06
17	117/84-109.ccls. and (silicon adj carbide or sic) and puls$4 near3 deposit$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 11:11

11	117/84-109.ccls. and puls$4 near3 deposit$4 not laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 11:53
22	(Sic or silicon adj carbide) same (vapor adj deposit$4) same puls$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 13:14
19	(vapor adj deposit$4) near2 puls$4 and (constant$4 or continuous$4 or stead$4) near4 (flow$4 or gas$4 or react$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 13:25
7	(vapor adj deposit$4) near2 puls$4 and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 13:27
3	puls$4 same (silicon adj carbide or sic) not laser and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 13:38
17	puls$4 near3 (deposit$4 or growth) and superlattice and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 13:49
14	puls$4 near3 (deposit$4 or growth) and superlattice not laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 15:20
13	puls$4 near3 (reactant) and (stead$4 or continuos$4 or constant$4) near3 (reactant)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 10:45
6	(si or silicon) near2 (sic or silicon adj carbide) same superlattice	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 15:18
20	(si or silicon) near2 (sic or silicon adj carbide) and (((si or silicon) near3 (reactant or source or gas) and (carbon) near2 (reactant or source)) same (puls$4 or continuous$4 or stead$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 15:24
36	(silicon or si or carbon) near3 puls$4 and (silicon adj carbide or sic) not laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 15:36
10	puls$4 near3 deposition same superlattice	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 15:39
7	puls$4 near3 deposition and superlattice not laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 15:41
6	superlattice same (silicon or si) near2 (silicon adj carbide or sic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 15:44

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-	51	(silicon adj carbide or sic) same puls$4 same deposit$4 not laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 16:13
-	32	(silicon adj carbide or sic) same (deposit$4) and (silicon or si) near3 (partial adj pressure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 16:14
-	3	((carbon or silicon or si) near2 (stead$4 or continuos$4 or constant$4) near2 (flow or pressure)) and (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 11:10
-	9	(silicon adj carbide or sic) same (vapor adj phase adj epitaxy or sulimation adj recrystallization or liquid adj deposition) same bulk	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:47
-	8	(silicon adj carbide or sic) adj bulk and (vapor adj phase adj epitaxy or sulimation adj recrystallization or liquid adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:51
-	92	(silicon adj carbide or sic) same (low adj pressure same CVD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:57
-	14	(silicon adj carbide or sic) same (low adj pressure same CVD) and growth adj rate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TIB	2002/11/25 14:28
-	89	(silicon adj carbide or sic) same (CVD) and growth adj rate same (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 14:40
-	35	(CVD) same growth adj rate same (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 15:04
-	9	(sic or silicon adj carbide) near2 seed same (gan or gallium adj nitride or diamond)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 15:09
-	3	(sic or silicon adj carbide) near2 seed and (gan or gallium adj nitride or diamond) same CVD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 15:24
-	19	dop$4 same superlattice same (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 17:09

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